

L Number	Hits	Search Text	DB	Time stamp
-	16216	etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:39
-	3482	etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) with (plasma vapor dry gas\$5) with (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 21:34
-	5720	etch\$3 near (Si silicon poly poly-Si polysilicon a-Si silicone) and etch\$3 near (plasma vapor dry gas\$5) and etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 21:36
-	953	etch\$3 adj (Si silicon poly poly-Si polysilicon a-Si silicone) same etch\$3 near (plasma vapor dry gas\$5) same etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 22:35
-	217	etch\$3 adj (Si silicon poly poly-Si polysilicon a-Si silicone) with etch\$3 near (plasma vapor dry gas\$5) with etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 21:39
-	8	etch\$3 adj (Si silicon poly poly-Si polysilicon a-Si silicone) near etch\$3 near (plasma vapor dry gas\$5) with etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 21:49
-	1830	(etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and PECVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 21:54
-	664	(etch\$3 near (Si silicon poly poly-Si polysilicon a-Si silicone) and etch\$3 near (plasma vapor dry gas\$5) and etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and PECVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 21:49
-	378	(etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) with (plasma vapor dry gas\$5) with (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and PECVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 21:49
-	95	(etch\$3 adj (Si silicon poly poly-Si polysilicon a-Si silicone) same etch\$3 near (plasma vapor dry gas\$5) same etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and PECVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 21:49
-	16	(etch\$3 adj (Si silicon poly poly-Si polysilicon a-Si silicone) with etch\$3 near (plasma vapor dry gas\$5) with etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and PECVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 21:49
-	648	(etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 22:59
-	249	(etch\$3 near (Si silicon poly poly-Si polysilicon a-Si silicone) and etch\$3 near (plasma vapor dry gas\$5) and etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 21:58

-	122	(etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) with (plasma vapor dry gas\$5) with (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 21:58
-	35	(etch\$3 adj (Si silicon poly poly-Si polysilicon a-Si silicone) same etch\$3 near (plasma vapor dry gas\$5) same etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 21:58
-	9	(etch\$3 adj (Si silicon poly poly-Si polysilicon a-Si silicone) with etch\$3 near (plasma vapor dry gas\$5) with etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 22:13
-	72	((etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)) and etch\$3 near (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 22:13
-	56	((etch\$3 near (Si silicon poly poly-Si polysilicon a-Si silicone) and etch\$3 near (plasma vapor dry gas\$5) and etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)) and etch\$3 near (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 22:14
-	16	((etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) with (plasma vapor dry gas\$5) with (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)) and etch\$3 near (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 22:14
-	0	((etch\$3 adj (Si silicon poly poly-Si polysilicon a-Si silicone) with etch\$3 near (plasma vapor dry gas\$5) with etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)) and etch\$3 near (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 22:14

-	7	((etch\$3 adj (Si silicon poly poly-Si polysilicon a-Si silicone) same etch\$3 near (plasma vapor dry gas\$5) same etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)) and etch\$3 near (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si) ("0633899").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 22:21
-	1		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 22:22
-	0	((("0633899").PN.) and etch\$3 with rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 22:24
-	0	((("0633899").PN.) and etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 22:25
-	10	((etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) with (plasma vapor dry gas\$5) with (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)) and etch\$3 near (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)) not (((etch\$3 adj (Si silicon poly poly-Si polysilicon a-Si silicone) same etch\$3 near (plasma vapor dry gas\$5) same etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si)) and etch\$3 near (a-Si amor-Si amorph-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 22:36
-	118	(etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si amor-Si amorp-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si) with (H hydrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:03
-	21	(etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si amor-Si amorp-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si) same ((H hydrogen) near (percent\$3 content amount ratio atom\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:04

-	25	(etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and (a-Si amor-Si amorp-Si amorphous-Si "Si.sub.amorph" "Si.sub.am" "Si.sub.amor" amor adj Silicon amorph adj Silicon amorphous adj Si) same ((H hydrogen) near (concentration percent\$3 content amount ratio atom\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:34
-	4073	(etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and etch\$3 near (preferential\$2 selective\$2 ratio) same (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:37
-	2882	((etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and etch\$3 near (preferential\$2 selective\$2 ratio) same (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")) and etch\$3 near (preferential\$2 selective\$2 ratio) with (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:37
-	608	((etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and etch\$3 near (preferential\$2 selective\$2 ratio) same (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")) and etch\$3 near (preferential\$2 selective\$2 ratio) near (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:38
-	210	((etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and etch\$3 near (preferential\$2 selective\$2 ratio) same (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")) and etch\$3 adj (preferential\$2 selective\$2 ratio) near (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:38
-	140	((etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) and (plasma vapor dry gas\$5) and (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and etch\$3 near (preferential\$2 selective\$2 ratio) same (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")) and etch\$3 adj (preferential\$2 selective\$2 ratio) adj (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:38
-	82	(etch\$3 near (Si silicon poly poly-Si polysilicon a-Si silicone) and etch\$3 near (plasma vapor dry gas\$5) and etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and etch\$3 adj (preferential\$2 selective\$2 ratio) adj (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:40
-	44	(etch\$3 with ((Si silicon poly poly-Si polysilicon a-Si silicone) with (plasma vapor dry gas\$5) with (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour))) and etch\$3 adj (preferential\$2 selective\$2 ratio) adj (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:40

-	12	(etch\$3 adj (Si silicon poly poly-Si polysilicon a-Si silicone) same etch\$3 near (plasma vapor dry gas\$5) same etch\$3 near (rate per \$3/s \$3/sec \$3/min \$3/minute \$3/h \$3/hr \$3/hour)) and etch\$3 adj (preferential\$2 selective\$2 ratio) adj (oxide nitride SiO2 Si3N4 "SiO.sub.2" "Si.sub.3 N.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/07 23:40
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